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WEST Search History

Hide Items Restore Clear Cancel

DATE: Friday, March 19, 2004

Hide?	Set Name	e Query	Hit Count
	DB=PGB	PB,USPT,EPAB,JPAB,DWPI,TDBD; PLUR=YES; C	OP=OR
	L36	134 and 111	57
	L35	134 and 111	57
. 🗀	L34	channel adj7 oxide	15617
	L33	cahnnel adj4 oxide	0
	L32	cahnnel adj4 oxide	0
	L31	5216262	22
	DB=PG	$PB, USPT, USOC, EPAB, JPAB, DWPI, TDBD; \ PLUR =$	YES; OP=OR
	L30	5216262	22
	L29	6472685	3
	DB = EPA	AB; PLUR=YES; OP=OR	
	L28	2347520	1
	DB=DW	PI; PLUR=YES; OP=OR	
	L27	L26 and 125	2
	L26	tsu.inv.	80
	L25	L24 and 123	63
	L24	barrier and silicon	5445
	L23	wang.inv.	40396
	L22	02103767	0
	L21	02/103767	0
	DB=PG	PB,USPT,EPAB,JPAB,DWPI,TDBD; PLUR=YES; (OP=OR
	L20	11 and 119	8
	L19	111 adj20 118	655
	L18	oxide or nitride o fluorine or carbon or carbide	6180325
	L17	6699771	1
	L16	12 and 114 and 115	16
	L15	oxygen or o?sub.\$	811012
	L14	silicon or si	1786914
	L13	17 and 15	56
	L12	111 and 118	0
	L11	superlattice	7764
	L10	12 and 18	0

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L9	band-modif\$5	0
L8	band adj modif\$5	262
L7	band adj modif\$5 or band-modi\$4	262
L6	12 and 15	36
L5	monolayer mono\$5 or atom\$5	1483361
L4	L3 and 12	27
L3	parallel	2304355
L2	superlattice adj6 channel	104
L1	superlattice adj6 channel	104

END OF SEARCH HISTORY

Refine Search

Search Results -

Terms	Documents		
L18 and L17	2		

US Pre-Grant Publication Full-Text Database

US Patents Full-Text Database

US OCR Full-Text Database

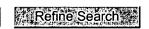
Database: EPO Abstracts Database JPO Abstracts Database

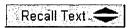
Derwent World Patents Index

IBM Technical Disclosure Bulletins

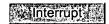
Search:

19	<u> </u> <u> </u> <u> </u> <u> </u> <u> </u> <u> </u>
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Search History

DATE: Friday, March 19, 2004 Printable Copy Create Case

Set Name side by side	Query	Hit Count	Set Name result set
DB=DWPI;	PLUR=YES; OP=OR		
<u>L19</u>	L18 and 117	2	<u>L19</u>
<u>L18</u>	lofgren.inv.	172	<u>L18</u>
<u>L17</u>	L16 and 115	20	<u>L17</u>
<u>L16</u>	wang.inv.	40396	<u>L16</u>
<u>L15</u>	tsu.inv.	80	<u>L15</u>
<u>L14</u>	2103767	7	<u>L14</u>
<u>L13</u>	02103767	0	<u>L13</u>
DB=PGPB,	USPT,EPAB,JPAB,DWPI,TDBD; PLUR	=YES; OP=OR	
<u>L12</u>	11 near20 12	5	<u>L12</u>
<u>L11</u>	L10 near10 11	34	<u>L11</u>
<u>L10</u>	tilt	166799	<u>L10</u>
<u>L9</u>	11 and 18	4	<u>L9</u>
<u>L8</u>	5679152	55	<u>L8</u>
<u>L7</u>	13 and 16	154	<u>L7</u>

WEST Search History



DATE: Friday, March 19, 2004

Hide? Set Name Query Hit C								
	DB=PG	PB, USPT, EPAB, JPAB, DWPI, TDBD; PLUR = YE	S: OP = OR					
	L20	11 and 119	8					
	L19	111 adj20 118	655					
	L18	oxide or nitride o fluorine or carbon or carbide	6180325					
	L17	6699771	1					
	L16	12 and 114 and 115	16					
	L15	oxygen or o?sub.\$	811012					
	L14	silicon or si	1786914					
	L13	17 and 15	56					
	L12	111 and 118	0					
	L11	superlattice	7764					
	L10	12 and 18	0					
	L9	band-modif\$5	0					
	L8	band adj modif\$5	262					
	L7	band adj modif\$5 or band-modi\$4	262					
	L6	12 and 15	36					
	L5	monolayer mono\$5 or atom\$5	1483361					
	L4	L3 and 12	27					
	L3	parallel	2304355					
	L2	superlattice adj6 channel	104					
	L1	superlattice adj6 channel	104					

END OF SEARCH HISTORY

Hit List



Search Results - Record(s) 1 through 16 of 16 returned.

☐ 1. Document ID: US 6559469 B1

Using default format because multiple data bases are involved.

L16: Entry 1 of 16

File: USPT

May 6, 2003

US-PAT-NO: 6559469

DOCUMENT-IDENTIFIER: US 6559469 B1

TITLE: Ferroelectric and high dielectric constant transistors

DATE-ISSUED: May 6, 2003

INVENTOR - INFORMATION:

COUNTRY NAME CITY STATE ZIP CODE Paz de Araujo; Carlos A. Colorado Springs CO McMillan; Larry D. Colorado Springs CO Colorado Springs Joshi; Vikram CO Solayappan; Narayan Colorado Springs CO Cuchiaro; Joseph D. Colorado Springs CO

US-CL-CURRENT: <u>257/15</u>; <u>257/16</u>, <u>257/17</u>, <u>257/18</u>, <u>257/19</u>, <u>257/20</u>, <u>257/21</u>, <u>257/22</u>, <u>257/295</u>, <u>257/E21.011</u>, <u>257/E21.272</u>, <u>257/E27.085</u>, <u>257/E27.104</u>

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Full	Title	Citation	Front	Raviem	Classification	Date	Reference	Semiletines	Attackness.	Claime	KMC	Drawt De
1 011	11111	Citation	1.10111	LICALCA	CIBSSINGBRIOTI	0010	mererence	ARTHUR THE SAME COURSE	William Colors Table Colors Colors	01011112	1000	

☐ 2. Document ID: US 6426536 B1

L16: Entry 2 of 16

File: USPT

Jul 30, 2002

US-PAT-NO: 6426536

DOCUMENT-IDENTIFIER: US 6426536 B1

TITLE: Double layer perovskite oxide electrodes

Full	Title	Citation	Front	Review	Classification	Date	Reference	Sequences	Affectments	Claims	KMC	Draw, De

☐ 3. Document ID: US 6355951 B1

L16: Entry 3 of 16

File: USPT

Mar 12, 2002

Record List Display Page 2 of 5

US-PAT-NO: 6355951

DOCUMENT-IDENTIFIER: US 6355951 B1

TITLE: Field effect semiconductor device

Full | Title | Citation | Front | Review | Classification | Date | Reference | <mark>இறுக்கில் இதுகிற்றனில் |</mark> Claims | KMC | Draw. De

☐ 4. Document ID: US 6294446 B1

L16: Entry 4 of 16

File: USPT

Sep 25, 2001

US-PAT-NO: 6294446

DOCUMENT-IDENTIFIER: US 6294446 B1

TITLE: Methods of manufacturing a high electron mobility transistor with a T-shaped

gate electrode

Full Title Citation Front Review Classification Date Reference Securios Attachments Claims KWC Draw. De

☐ 5. Document ID: US 5952672 A

L16: Entry 5 of 16

File: USPT

Sep 14, 1999

US-PAT-NO: 5952672

DOCUMENT-IDENTIFIER: US 5952672 A

TITLE: Semiconductor device and method for fabricating the same

Full Title Citation Front Review Classification Date Reference Sequences Attachments Claims KMC Draw. De

☐ 6. Document ID: US 5760418 A

L16: Entry 6 of 16

File: USPT

Jun 2, 1998

US-PAT-NO: 5760418

DOCUMENT-IDENTIFIER: US 5760418 A

TITLE: GaAs power semiconductor device operating at a low voltage and method for

fabricating the same

Full Title Citation Front Review Classification Date Reference இல்றின்ற Alfachinanis Claims KMC Draw. De

☐ 7. Document ID: US 5639677 A

L16: Entry 7 of 16

File: USPT

Jun 17, 1997

US-PAT-NO: 5639677

DOCUMENT-IDENTIFIER: US 5639677 A

TITLE: Method of making a gaAs power semiconductor device operating at a low

Record List Display

voltage

Full Title Citation Front Review Classification Date Reference Sequences Attachments Claims KMC Draw De □ 8. Document ID: US 5432356 A

L16: Entry 8 of 16

File: USPT

Jul 11, 1995

US-PAT-NO: 5432356

DOCUMENT-IDENTIFIER: US 5432356 A

TITLE: Semiconductor heterojunction floating layer memory device and method for storing information in the same

Full Title Citation Front Review Classification Date Reference Sequences Attachineris Claims KMC Draw De

☐ 9. Document ID: US 5430310 A

L16: Entry 9 of 16

File: USPT

Jul 4, 1995

US-PAT-NO: 5430310

DOCUMENT-IDENTIFIER: US 5430310 A

TITLE: Field effect transistor

Full Title Citation Front Review Classification Date Reference Seguences Attachments Claims KMC Draw De ☐ 10. Document ID: US 5155053 A

L16: Entry 10 of 16

File: USPT

Oct 13, 1992

US-PAT-NO: 5155053

DOCUMENT-IDENTIFIER: US 5155053 A

TITLE: Method of forming T-gate structure on microelectronic device substrate

Full Title Citation Front Review Classification Date Reference Sequences Attachments Claims KMC Draw De

☐ 11. Document ID: US 5055887 A

L16: Entry 11 of 16

File: USPT

Oct 8, 1991

US-PAT-NO: 5055887

DOCUMENT-IDENTIFIER: US 5055887 A

TITLE: FET with a super lattice channel

Full Title Citation Front Review Classification Date Reference Sequences Attachments Claims KMC Draw. De

. □ 12. Document ID: US 5021839 A

L16: Entry 12 of 16

File: USPT

Jun 4, 1991

US-PAT-NO: 5021839

DOCUMENT-IDENTIFIER: US 5021839 A

TITLE: FET with a super lattice channel

Full Title Citation Front Review Classification Date Reference **Securities Accomments:** Claims KMC Draw. De

☐ 13. Document ID: US 5008211 A

L16: Entry 13 of 16

File: USPT

Apr 16, 1991

US-PAT-NO: 5008211

DOCUMENT-IDENTIFIER: US 5008211 A

TITLE: Method for forming FET with a super lattice channel

Full Title Citation Front Review Classification Date Reference Segmences Attainments Claims KWC Draw. De

☐ 14. Document ID: US 4945393 A

L16: Entry 14 of 16

File: USPT

Jul 31, 1990

US-PAT-NO: 4945393

DOCUMENT-IDENTIFIER: US 4945393 A

TITLE: Floating gate memory circuit and apparatus

Full Title Citation Front Review Classification Date Reference **Segmences Attachments** Claims KMC Draw. De

☐ 15. Document ID: US 4905063 A

L16: Entry 15 of 16

File: USPT

Feb 27, 1990

US-PAT-NO: 4905063

DOCUMENT-IDENTIFIER: US 4905063 A

TITLE: Floating gate memories

Full Title Citation Front Review Classification Date Reference இன்றுத்து அத்து அறிக்கு Claims KWIC Draw. De

☐ 16. Document ID: US 4799087 A

L16: Entry 16 of 16

File: USPT

Jan 17, 1989

US-PAT-NO: 4799087